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(54) Title: SEMICONDUCTOR CAVITY

(54) 发明名称: 半导体腔室

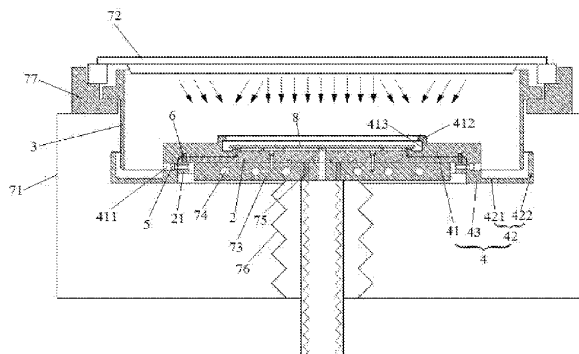


图 2

(57) **Abstract:** Provided in the present invention is a semiconductor cavity. The semiconductor cavity comprises a cavity body, and a first shielding member and a liftable base assembly, which are arranged in the cavity body, wherein the first shielding member is fixedly connected to an inner peripheral wall of the cavity body and is arranged in a circumferential direction of the inner peripheral wall of the cavity body; the base assembly comprises a base body, a second shielding member and a positioning structure; the base body is coaxially arranged with the cavity body and used for bearing a wafer; the second shielding member is arranged on the base body in a circumferential direction of the base body; when the base body ascends to a process position, the second shielding member and the first shielding member are partially overlapped, and the part of the second shielding member that is overlapped with the first shielding member is located on the side of the first shielding member that faces away from the base body; and the positioning structure is arranged between the base body and the second shielding member and is used for positioning the relative position of the base body and the second shielding member. By means of the semiconductor cavity provided by the present invention, a wafer can be prevented from being shielded, thus the uniformity of a wafer deposition film is increased, and therefore the chip performance is improved.

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TD, TG)。

本国际公布:

— 包括国际检索报告 (条约第21条(3))。

(57) 摘要: 本发明提供一种半导体腔室, 半导体腔室包括腔体和设置在腔体中的第一遮挡件和可升降的基座组件, 其中, 第一遮挡件与腔体的内周壁固定连接, 且沿腔体的内周壁的周向设置; 基座组件包括基座本体、第二遮挡件和定位结构, 基座本体与腔体同轴设置, 用于承载晶圆; 第二遮挡件沿基座本体的周向设置在基座本体上, 基座本体位于上升至工艺位时, 第二遮挡件与第一遮挡件部分重叠设置, 且第二遮挡件的与第一遮挡件相互重叠的部分位于第一遮挡件背离基座本体的一侧; 定位结构设置在基座本体与第二遮挡件之间, 用于对基座本体与第二遮挡件的相对位置进行定位。本发明提供的半导体腔室能够避免遮挡晶圆, 提高晶圆沉积薄膜的均匀性, 从而改善芯片性能。